CLAIMS:

1. A method used in forming a memory array comprising strings of memory cells, comprising:

forming a stack comprising vertically-alternating first tiers and second tiers;

forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;

forming a wall in individual of the trenches laterally-between immediately laterally adjacent of the laterally-spaced memory-block regions, the forming of the wall comprising:

lining sides and bottoms of trenches with a layer of insulative material comprising an insulative nitride, an elemental-form boron, or both; and

forming a core material in the trenches to span laterally, wherein the layer of insulative material surrounds the core material at the sides and the bottoms of the trenches completely.

2. The method of claim 1 wherein the layer of insulative material comprises one of more members of the group consisting of silicon nitride, boron nitride, carbon nitride, silicon nitride carbide, and germanium nitride.

3. The method of claim 1 wherein the layer of insulative material is devoid of oxygen.

4. The method of claim 1 comprising:

before forming the wall in the individual trenches, isotropically etching away and replacing sacrificial material that is in the first tiers with conducting material of individual conductive lines;

forming individual memory cells of the strings of memory cells to comprise channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the first tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual first tiers, forming the channel-material strings before forming the conducting material of the individual conductive lines; and

after the replacing, forming the wall in the individual trenches.

5. The method of claim 1,

wherein the individual trenches having an uppermost minimum lateral width in a vertical cross-section, the insulative material layer on each side of the core material having a lateral width of 1% to 20% of the uppermost minimum lateral width in the vertical cross-section.

6. A method used in forming a memory array comprising strings of memory cells, comprising:

forming a stack comprising vertically-alternating first tiers and second tiers;

forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;

through the trenches, isotropically etching away and replacing sacrificial material that is in the first tiers with conducting material of individual conductive lines;

forming individual memory cells of the strings of memory cells to comprise channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the first tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual first tiers, forming the channel-material strings before forming the conducting material of the individual conductive lines;

after the replacing, forming a wall in individual of the trenches laterally-between immediately adjacent of the laterally-spaced memory-block regions, the forming of the wall comprising;

lining sides and bottoms of the trenches with a layer of insulative material comprising an insulative nitride, an elemental-form boron, or both, wherein the layer of insulative material is directly against the conducting material of the individual conductive lines; and

forming a core material in the trenches spanning laterally, wherein the layer of insulative material surrounds the core material at the sides and the bottoms of the trenches completely, the forming of the core material comprising:

forming a laterally-outer silicon dioxide that is directly against the layer of insulative material; and

forming polysilicon directly against and to span laterally-between said laterally-outer silicon dioxide.